



NPN POWER TRANSISTORS

COMPLEMENTARY TO THE D43C SERIES

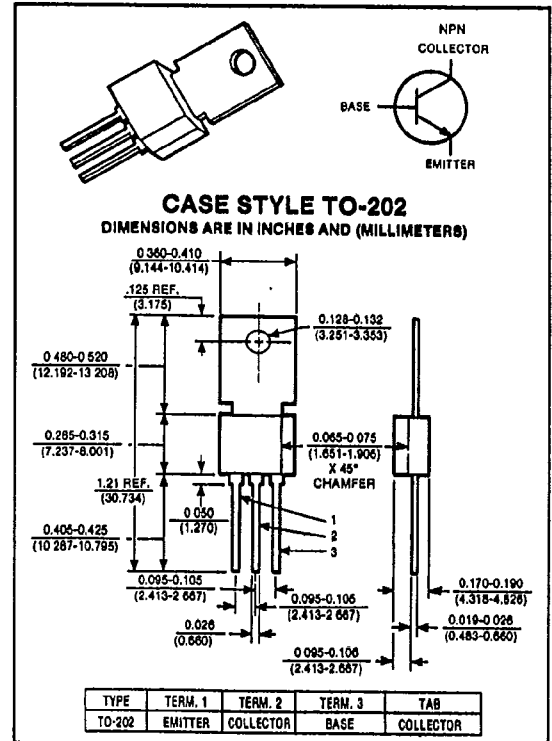
D42C Series

30-80 VOLTS
3 AMP, 12.5 WATTS

The General Electric D42C is a power transistor designed for various specific and general purpose applications, such as: output and driver stages of amplifiers operating at frequencies from DC to greater than 1.0 MHz; series, shunt and switching regulators; low and high frequency inverters/converters; and many others.

Features:

- High free-air power dissipation
- NPN complement to D43C PNP
- Low collector saturation voltage (0.5V typ. @ 3.0A I_C)
- Excellent linearity
- Fast Switching



maximum ratings ($T_A = 25^\circ\text{C}$) (unless otherwise specified)

RATING	SYMBOL	D42C1, 2, 3	D42C4, 5, 6	D42C7, 8, 9	D42C10, 11, 12	UNITS
Collector-Emitter Voltage	V_{CEO}	30	45	60	80	Volts
Collector-Emitter Voltage	V_{CES}	40	55	70	90	Volts
Emitter Base Voltage	V_{EBO}	5	5	5	5	Volts
Collector Current — Continuous	I_C	3	3	3	3	A
Peak(1)	I_{CM}	5	5	5	5	A
Base Current — Continuous	I_B	2	2	2	2	A
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ @ $T_C = 25^\circ\text{C}$	P_D	2.1 12.5	2.1 12.5	2.1 12.5	2.1 12.5	Watts
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	-55 to +150	-55 to +150	-55 to +150	$^\circ\text{C}$

thermal characteristics

Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	60	60	60	60	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	10	10	10	10	$^\circ\text{C/W}$
Maximum Lead Temperature for Soldering Purposes: $\frac{1}{8}$ " from Case for 5 Seconds	T_L	+260	+260	+260	+260	$^\circ\text{C}$

(1) Pulse Test Pulse Width = 300ms Duty Cycle \leq 2%.

electrical characteristics ($T_C = 25^\circ C$) (unless otherwise specified)

CHARACTERISTIC	SYMBOL	MIN	TYP	MAX	UNIT
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off characteristics⁽¹⁾

Collector-Emitter Sustaining Voltage ($I_C = 100mA$)	D42C1, 2, 3 D42C4, 5, 6 D42C7, 8, 9 D42C10, 11, 12	$V_{CEO(sus)}$	30 45 60 80	— — — —	— — — —	Volts
Collector Cutoff Current ($V_{CE} = \text{Rated } V_{CES}$)		I_{CES}	—	—	10	μA
Emitter Cutoff Current ($V_{EB} = 5V$)		I_{EBO}	—	—	100	μA

second breakdown

Second Breakdown with Base Forward Biased	FBSOA	SEE FIGURES 3 & 4
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on characteristics⁽¹⁾

DC Current Gain ($I_C = 200mA, V_{CE} = 1V$)	D42C1, 4, 7, 10 D42C2, 5, 8, 11 D42C3, 6, 9, 12	h_{FE}	25 100 40	— — —	— 220 120	—
($I_C = 1A, V_{CE} = 1V$) ($I_C = 2A, V_{CE} = 1V$)	D42C1, 4, 7, 10 D42C2, 5, 8, 11 D42C3, 6, 9, 12	h_{FE}	10 20 20	— — —	— — —	—
Collector-Emitter Saturation Voltage ($I_C = 1A, I_B = 50mA$)	D42C2, 5, 8, 11 D42C3, 6, 9, 12	$V_{CE(sat)}$	— —	— —	0.5 0.5	Volts
($I_C = 1A, I_B = 100mA$)	D42C1, 4, 7, 10	$V_{CE(sat)}$	—	—	0.5	Volts
Base-Emitter Saturation Voltage ($I_C = 1A, I_B = 100mA$)		$V_{BE(sat)}$	—	—	1.3	Volts

dynamic characteristics

Collector Capacitance ($V_{CB} = 10V, f = 1MHz$)	C_{CBO}	—	—	100	pF
Current-Gain — Bandwidth Product ($I_C = 20mA, V_{CE} = 4V$)	f_T	—	50	—	MHz

switching characteristics

Resistive Load					
Delay Time + Rise Time	$I_C = 1A, I_{B1} = I_{B2} = 0.1A,$ $V_{CC} = 30V, t_p = 25 \mu sec$	$t_d + t_r$	—	100	—
Storage Time		t_s	—	500	—
Fall Time		t_f	—	75	—

(1) Pulse Test PW = 300ms Duty Cycle \leq 2%.

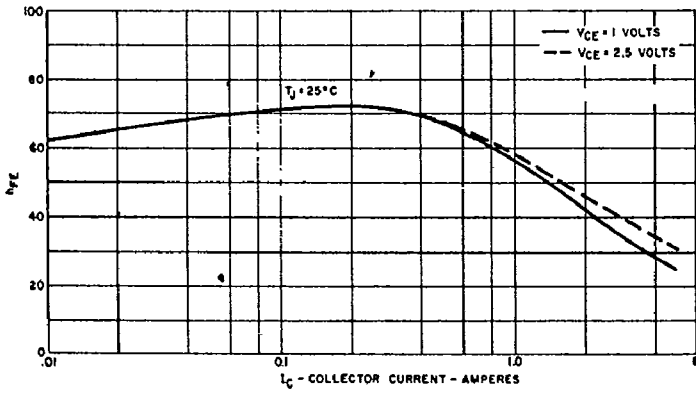


FIG. 1 TYPICAL h_{FE} VS. I_C

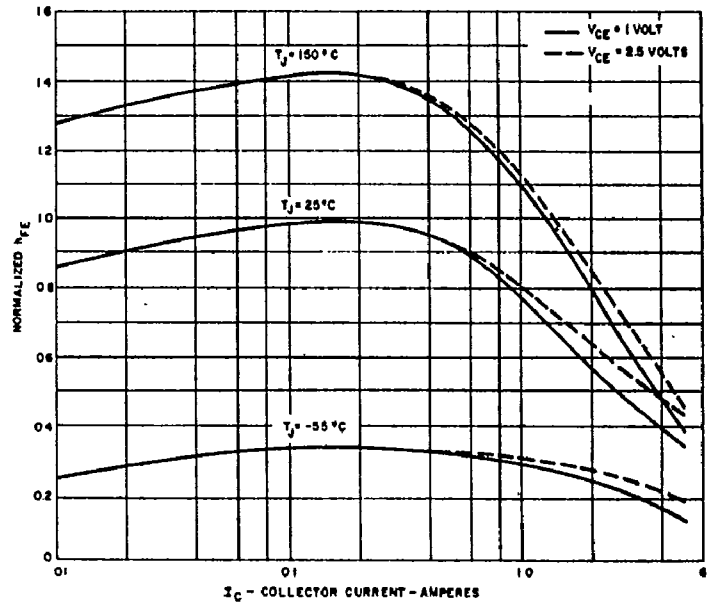


FIG. 2 TYPICAL NORMALIZED h_{FE} VS. I_C

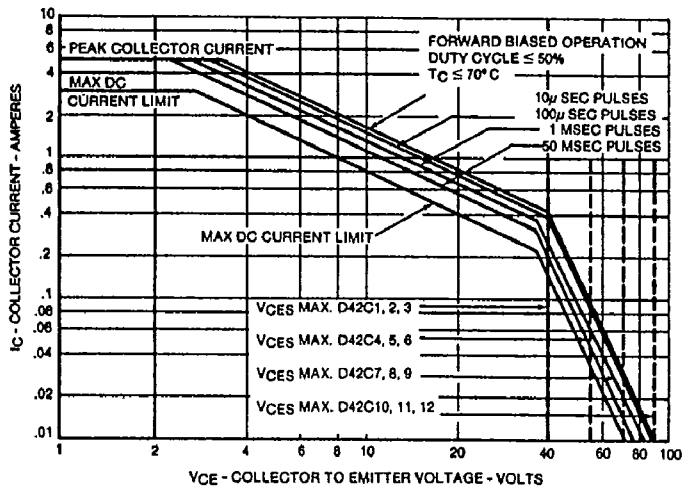


FIG. 3 SAFE REGION OF OPERATION

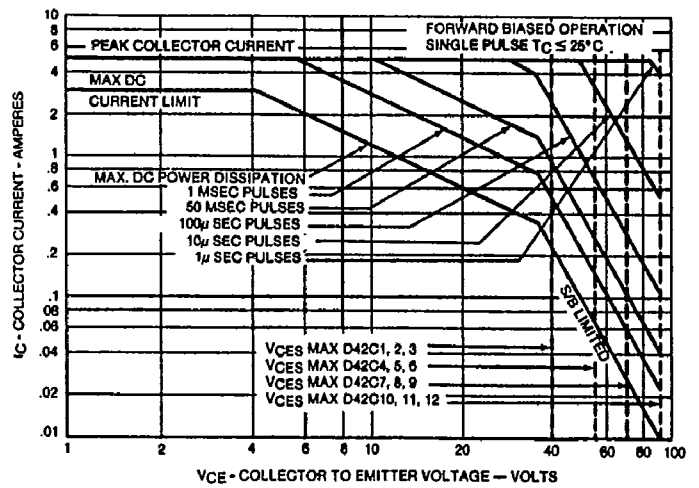


FIG. 4 SAFE REGION OF OPERATION

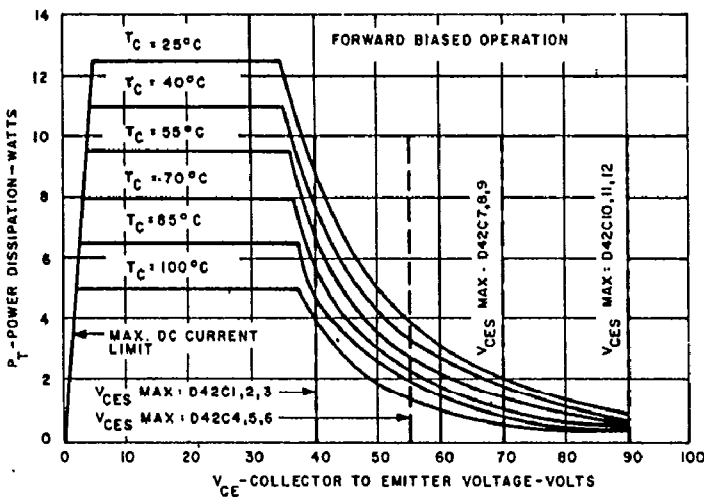


FIG. 5 MAXIMUM PERMISSIBLE DC POWER DISSIPATION

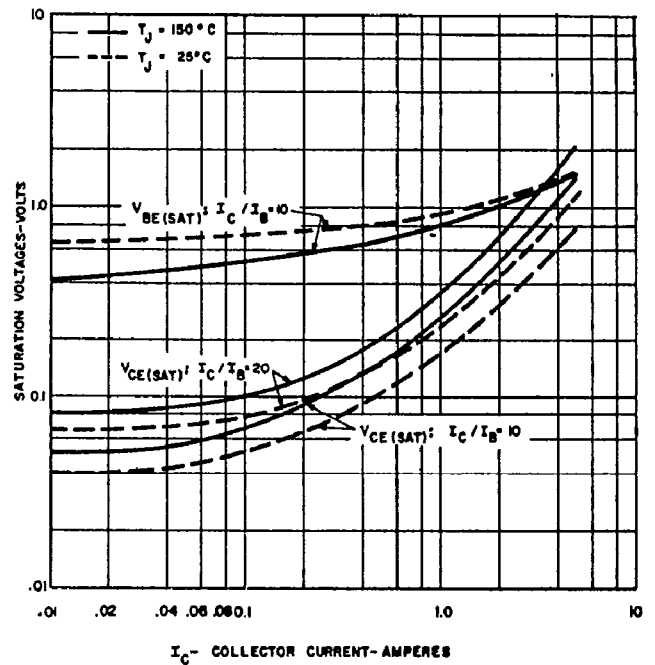


FIG. 6 TYPICAL SATURATION VOLTAGE CHARACTERISTICS

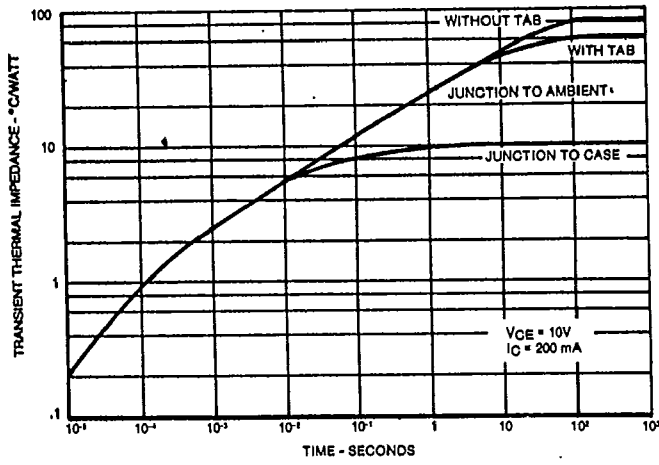


FIG. 7 MAXIMUM TRANSIENT THERMAL IMPEDANCE

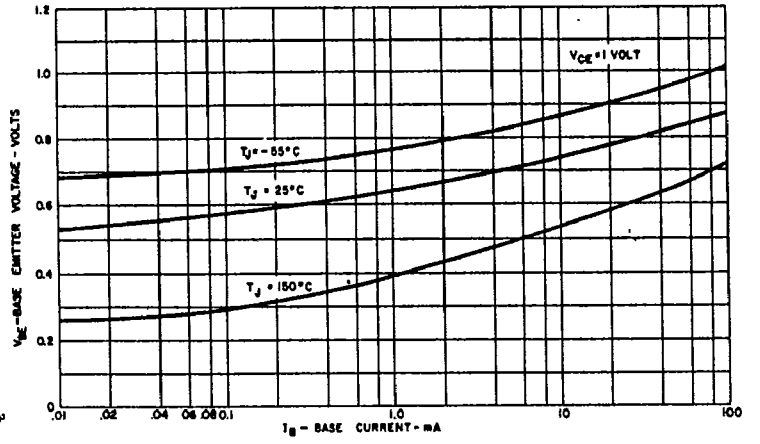


FIG. 8 TYPICAL INPUT CHARACTERISTICS

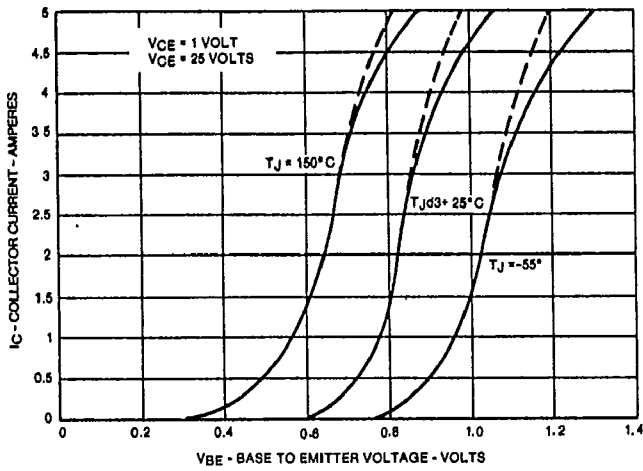


FIG. 9

TYPICAL TRANSCONDUCTANCE CHARACTERISTICS

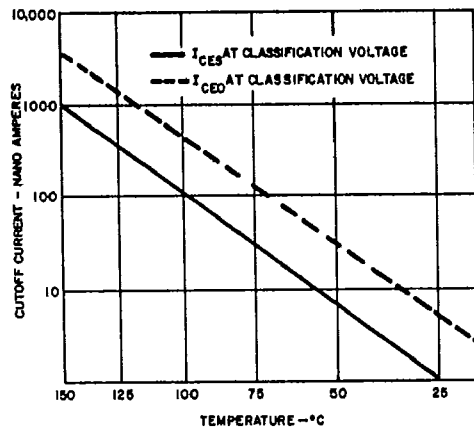


FIG. 10

TYPICAL I_{CEO}, I_{CES} VS. TEMPERATURE